IN THE CLAIMS:

Kindly replace the claims of record with the following full set of claims:

1. (Currently amended)   An impedance transformation circuit (10; 11a; 11b; 12) with a first contact pad (51) and a second contact pad (52) being spaced-apart and formed on a substrate (20), comprising:

at least a first circuit element (40) providing a contract area (41) formed on the substrate (20) and being arranged adjacent and between the first (51) and the second (52) contact pad,

a first wire element (310) extending over the substrate (20) connecting the first contact pad (51) and a first end portion (41a) of the contact area (410 of the first circuit element (41), and

at least a second wire element (32) extending over the substrate (20) connecting the second contract pad (52) and a second end portion (41b) of the contact area (41) of the first circuit element (40), wherein the contact area (41) of the first circuit element (41) is shaped to provide a capacitive connection with a predetermined capacitance between the contract area (41) and a fixed reference potential, and

a second circuit element located on the substrate and having a first terminal and a second terminal, the second circuit element having a predetermined capacitance value and being arranged to provide a capacitive connection between the first contact pad and the second contact pad, wherein the first terminal is connected to the first contact pad and the second terminal is connected to the second contact pad.

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2. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1, wherein the first wire element (31) and the at least second wire element (32) have the same shape and are arranged substantially in parallel to each other.

3. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1, wherein the first contact pad (51) and the second contact pad (52) are located at opposite sides of the contact area (41) of the at least first circuit element (40).

4. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1, wherein the first circuit element (40) is a metal oxide semiconductor (MOS) capacitor.

5. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1, wherein there the substrate (20) is arranged on a metal layer (22), which is connected to a fixed reference potential.

6. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1, wherein the fixed reference potential is a ground potential.

7. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1, wherein the wire elements (31, 32, 31, 32, 36, 31, 32, 33, 34) are bond wires.

8. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1, wherein the first contact pad (51) is an input connection and the second contact pad (52) is an output connection of the impedance transformation circuit (10, 11a, 11b, 12).

9. (cancelled)

10. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1 [[9]], wherein at least one of the first terminal and the second terminal is connected to the respective one of the first and second contact pads (51, 52) via a wire element (36) extending over the substrate.

11. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1 [[9]], wherein the second circuit element (60) is a thin film capacitor.

12. (Currently amended) The impedance transformation circuit (10; 11a; 11b; 12) according to claim 1 [[9]], wherein the second circuit element is a capacitor formed by coupled strip lines on the substrate.

13. (Withdrawn) A multi-coupled wire impedance transformation circuit (12), comprising at least a first (16) and a second (18) impedance transformation circuits according to claim 1 arranged adjacent to each other on a single substrate (20), wherein the first (16)

and the second (18) impedance transformation circuits are electrically connected in

parallel to each other by the respective first contact pads (51, 53) and the second contact

pads (52, 54) of the first and second impedance transformation circuits (16, 18).

14. (Withdrawn)   The multi-coupled wire impedance transformation circuit (12)

according to claim 13, wherein the wire elements (31, 32, 33, 34) are arranged with

respect to each other such that there is provided a predetermined capacitive and inductive

coupling between adjacent wire elements.

15. (Currently amended) A radio frequency device, which comprises functional radio

frequency circuitry, having at least one of a passive circuit block for at least one of

impedance matching and frequency filtering, the passive circuit block comprising an

impedance transformation circuit comprising:

        at least a first circuit element providing a contract area formed on the substrate

and being arranged adjacent and between the first and the second contact pad,

        a first wire element extending over the substrate connecting the first contact pad

and a first end portion of the contact area of the first circuit element , and

        at least a second wire element extending over the substrate connecting the

second contract pad and a second end portion of the contact area of the first circuit

element , wherein the contact area of the first circuit element is shaped to provide a

capacitive connection with a predetermined capacitance between the contract area and a

fixed reference potential, and

_____   a second circuit element located on the substrate and having a first terminal and a
second terminal, the second circuit element having a predetermined capacitance value
and being arranged to provide a capacitive connection between the first contact pad and
the second contact pad, wherein the first terminal is connected to the first contact pad and
the second terminal is connected to the second contact pad.
~~according to claim 1~~.

16. (Previously presented) The radio frequency device according to claim 15, wherein the
radio frequency device is a mobile phone, a base station for radio access networks, or a
signal converter in cable television (CATV) receivers.